TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

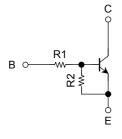
## RN1101FT, RN1102FT, RN1103FT RN1104FT, RN1105FT, RN1106FT

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

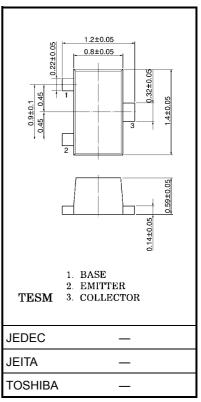
Unit: mm

- High-density mount is possible because of devices housed in very thin TESM packages.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Wide range of resistor values are available to use in various circuit designs.
- Complementary to RN2101FT~2106FT

### **Equivalent Circuit and Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN1101FT	4.7	4.7
RN1102FT	10	10
RN1103FT	22	22
RN1104FT	47	47
RN1105FT	2.2	47
RN1106FT	4.7	47



#### **Maximum Ratings (Ta = 25°C)**

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN1101FT~1106FT	$V_{CBO}$	50	V	
Collector-emitter voltage	KINTTO II TATTOOLT	$V_{CEO}$	CEO 50		
Emitter-base voltage	RN1101FT~1104FT	$V_{EBO}$	10	V	
	RN1105FT, RN1106FT	vEBO.	5		
Collector current		IC	100	mA	
Collector power dissipation	RN1101FT~1106FT	P <sub>C</sub> (Note)	100	mW	
Junction temperature	KNITOTET~TTOOFT	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−55~150</b>	°C	

Note: Total rating



# **Electrical Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN1101FT~1106FT	I <sub>CBO</sub>	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0	_	_	100	nA
		I <sub>CEO</sub>	V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0	_	_	500	
	RN1101FT	- I <sub>EBO</sub>	V <sub>EB</sub> = 10 V, I <sub>C</sub> = 0	0.82	_	1.52	mA
	RN1102FT			0.38	_	0.71	
Emitter out off ourrent	RN1103FT			0.17	_	0.33	
Emitter cut-off current	RN1104FT			0.082	_	0.15	
	RN1105FT		V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	0.078	_	0.145	
	RN1106FT			0.074	_	0.138	
	RN1101FT			30	_	_	
	RN1102FT			50	_	_	
	RN1103FT	1 .	.,	70	_	_	
DC current gain	RN1104FT	- h <sub>FE</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	80	_	_	
	RN1105FT	- -		80	_	_	
	RN1106FT			80	_	_	
Collector-emitter saturation voltage	RN1101FT~1106FT	V <sub>CE</sub> (sat)	$I_C = 5 \text{ mA},$ $I_B = 0.25 \text{ mA}$	_	0.1	0.3	٧
Input voltage (ON)	RN1101FT	Vi (on)	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	1.1	_	2.0	V
	RN1102FT			1.2	_	2.4	
	RN1103FT			1.3	_	3.0	
	RN1104FT			1.5	_	5.0	
	RN1105FT			0.6	_	1.1	
	RN1106FT			0.7	_	1.3	
Input voltage (OFF)	RN1101FT~1104FT	V <sub>I (OFF)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.1 mA	1.0	_	1.5	V
	RN1105FT, 1106FT			0.5	_	0.8	
Transition frequency	RN1101FT~1106FT	f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	_	250	_	MHz
Collector output capacitance	RN1101FT~1106FT	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0,$ f = 1 MHz	_	3	6	pF
	RN1101FT	R1	_	3.29	4.7	6.11	kΩ
	RN1102FT			7	10	13	
Input resistor	RN1103FT			15.4	22	28.6	
	RN1104FT			32.9	47	61.1	
	RN1105FT			1.54	2.2	2.86	
	RN1106FT			3.29	4.7	6.11	
Resistor ratio	RN1101FT~1104FT	R1/R2	_	0.9	1.0	1.1	
	RN1105FT			0.0421	0.0468	0.0515	
	RN1106FT			0.09	0.1	0.11	

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Type Name	Marking
RN1101FT	Type name XA
RN1102FT	Type name XB
RN1103FT	Type name X C
RN1104FT	Type name X D
RN1105FT	Type name XE
RN1106FT	Type name XF

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